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				Application Number	09/921,518
				Filing Date	August 1, 2001
				First Named Inventor	John T. Moore
				Art Unit	2818
				Examiner Name	P. Dang
Sheet	1	of	1	Attorney Docket Number	M4065.0696/P696

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
P.D.	A	6,469,364 B1	10/22/2002	Kozicki	
P.D.	B	US 2002/0168820 A1	11/14/2002	Kozicki et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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Examiner Signature	PHUC T. DANG	Date Considered	8/4/03
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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: John T. Moore			
				FILING DATE August 1, 2001	GROUP 2818		
U.S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
PD	AA	10/061,825	Gilton et al. (as filed and amended)			01/31/2002	
PD	AB	10/077,867	Campbell et al. (as filed)			02/20/2002	
PD	AC	10/232,757	Li, et al. (as filed)			08/29/2002	
	AD						
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FOREIGN PATENT DOCUMENTS							
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						Yes	No
	AL						
	AM						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
PD	AN		Owens et al., <i>Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures</i> , NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (Academic Press, 1989).				
PD	AO		Safran et al., <i>TEM study of Ag<sub>2</sub>Se developed by the reaction of polycrystalline silver films and selenium</i> , 317 THIN SOLID FILMS, pp. 72-76 (1998).				
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U.S. PATENT DOCUMENTS									
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate		
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							Yes	No	
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PD	AN		Somogyi et al., <i>Temperature Dependence of the Carrier Mobility in Ag<sub>2</sub>Se Layers Grown on</i>						
			NaCl and SiO <sub>2</sub> Substrates, 74 ACTA PHYSICA HUNGARICA, No. 3, pp. 243-255 (1984).						
PD	AO		Tal et al., <i>Multilevel Ge-Se film based resist systems</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY,						
			pp. 32-39 (March 1982).						
PP	AP		Tal et al., <i>Submicron optical lithography using an inorganic resist/polymer bilayer scheme</i> ,						
			17 J. Vac. Sci. Technol., No. 5, pp. 1169-1176 (Sept./Oct. 1980).						
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	AM							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
PD	AH		Yoshikawa et al., <i>Dry development of Se-Ge inorganic photoresist</i> , 36 APPL. PHYS. LETT., No. 1; pp. 107-109 (January 1980).					
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